

IMPROVED PROCESS FOR DEPOSITION OF SEMICONDUCTOR FILMS

Abstract of the Disclosure

Chemical vapor deposition processes utilize chemical precursors that allow for the deposition of thin films to be conducted at or near the mass transport limited regime. The processes have high deposition rates yet produce more uniform films, both compositionally and in thickness, than films prepared using conventional chemical precursors. In preferred embodiments, trisilane is employed to deposit thin films containing silicon are useful in the semiconductor industry in various applications such as transistor gate electrodes.

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